

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Duy-Phach Vu, Brenda D. Dingle, Jason E. Dingle and Ngwe Cheong

Continuation Application  
of Application No.: 09/465,140

Filed: December 16, 1999

Title: METHOD OF FORMING AN ACTIVE MATRIX DISPLAY

Date: <u>07-15-03</u> EXPRESS MAIL LABEL NO. <u>EN 2149.3561345</u>
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INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

This Information Disclosure Statement is submitted:

- ☐ under 37 CFR 1.129(a), or  
(First/Second submission after Final Rejection)
- ☒ under 37 CFR 1.97(b), or  
(Within any one of the following time periods: three months of filing national application (other than a CPA) or date of entry of the national stage in an international application; or before the mailing date of a first office action on the merits in a non-provisional application, including a CPA, or a Request for Continued Examination).
- ☐ under 37 CFR 1.97(c) together with either:
- ☐ a Statement under 37 CFR 1.97(e), as checked below, or
- ☐ a \$180.00 fee under 37 CFR 1.17(p), or  
(After the 37 CFR 1.97(b) time period, but before final action or notice of allowance, whichever occurs first)
- ☐ under 37 CFR 1.97(d) together with:
- ☐ a Statement under 37 CFR 1.97(e), as checked below, and
- ☐ a \$180.00 fee under 37 CFR 1.17(p), or  
(Filed after final action or notice of allowance, whichever occurs first, but on or before payment of the issue fee)
- ☐ under 37 CFR 1.97(i):  
Applicant requests that the IDS and cited reference(s) be placed in the application filewrapper.  
(Filed after payment of issue fee)

Statement Under 37 CFR 1.97(e)

- ☐ Each item of information contained in this Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement; or
- ☐ No item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the undersigned, after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of this Information Disclosure Statement.

Statement Under 37 CFR 1.704(d) (Patent Term Adjustment)

Applies to original applications (other than design) filed on or after May 29, 2000

- ☐ Each item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart application and this communication was not received by any individual designated in § 1.56(c) more than thirty days prior to the filing of the Information Disclosure Statement.
- ☒ Enclosed herewith is form PTO-1449:
  - ☐ Copies of the cited references are enclosed.
  - ☒ Copies of cited references are enclosed except those entered in prior application, U.S. Application No. 09/465,140, to which priority under 35 U.S.C. 120 is claimed. The earlier application contains copies of the cited references.
  - ☐ The listed references were cited in the enclosed International Search Report in a counterpart foreign application.
  - ☐ The "concise explanation" requirement (non-English references) for reference(s) [       ] under 37 CFR 1.98(a)(3) is satisfied by:
    - ☐ the explanation provided on the attached sheet.
    - ☐ the explanation provided in the Specification.
    - ☐ submission of the enclosed International Search Report.
    - ☐ submission of the enclosed English-language version of a foreign Search Report and/or foreign Office Action.
    - ☐ the enclosed English language abstract.

☐ Applicant requests that the following non-published pending applications be considered:

Examiner's  
Initials

\_\_\_\_\_ U.S. Patent Application No. [ ], by [inventor(s)], filed [ ], Docket No.: [ ]

\_\_\_\_\_ U.S. Patent Application No. [ ], by [inventor(s)], filed [ ], Docket No.: [ ]

\_\_\_\_\_ U.S. Patent Application No. [ ], by [inventor(s)], filed [ ], Docket No.: [ ]

\_\_\_\_\_  
Examiner

\_\_\_\_\_  
Date

☐ A copy of each above-cited application, including the current claims, is enclosed.

☐ A copy of each above-cited application, including the current claims, is enclosed, except those entered in prior application, U.S. Application No. [ ], to which priority under 35 U.S.C. 120 is claimed.

The Examiner is requested to return a copy of the above list of pending applications indicating which references were considered with the next office communication.

It is requested that the information disclosed herein be made of record in this application.

Method of payment:

☐ A check for the fee noted above is enclosed, or the fee has been included in the check with the accompanying Reply. A copy of this Statement is enclosed.

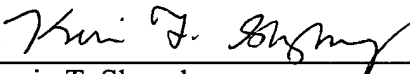
☐ Please charge Deposit Account 08-0380 in the amount of \$[ ]. A copy of this Statement is enclosed.

☒ Please charge any deficiency in fees and credit any overpayment to Deposit Account 08-0380.

Respectfully submitted,

HAMILTON, BROOK, SMITH & REYNOLDS, P.C.

By

  
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Kevin T. Shaughnessy  
Registration No.: 51,014  
Telephone: (978) 341-0036  
Facsimile: (978) 341-0136

Concord, MA 01742-9133

Dated: 7/15/03

PTO-1449 REPRODUCED  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  <b>July 15, 2003</b>  (Use several sheets if necessary)	ATTORNEY DOCKET NO. 0717.1063-007		CONTINUATION OF APPLICATION No. 09/465,140	
	APPLICANT Duy-Phach Vu, et al.			
	FILING DATE	CONFIRMATION NO.	GROUP	

U.S. PATENT DOCUMENTS				
EXAM- INER INI- TIAL	REF. NO.	DOCUMENT NUMBER	ISSUE DATE / PUBLICATION DATE	NAME
	AA	4,575,854	03-11-86	Martin
	AB	4,727,047	02-23-88	Bozler, <i>et al.</i>
	AC	4,774,205	09-27-88	Choi, <i>et al.</i>
	AD	4,769,680	09-06-88	Resor, III, <i>et al.</i>
	AE	4,808,983	02-28-89	Benjamin, <i>et al.</i>
	AF	4,838,654	06-13-89	Hamaguchi, <i>et al.</i>
	AG	4,846,931	07-11-89	Gmitter, <i>et al.</i>
	AH	4,855,255	08-08-89	Goodhue
	AI	4,863,877	09-05-89	Fan, <i>et al.</i>
	AJ	4,870,475	09-26-89	Endo, <i>et al.</i>
	AK	4,883,561	11-28-89	Gmitter, <i>et al.</i>
	AA2	4,935,792	06-19-90	Tanaka, <i>et al.</i>
	AB2	4,961,629	10-09-90	Kato
	AC2	4,965,565	10-23-90	Noguchi
	AD2	4,979,002	12-18-90	Pankove
	AE2	5,045,895	09-03-91	Yoshida, <i>et al.</i>
	AF2	5,073,806	12-17-91	Idei
	AG2	5,084,905	01-28-92	Sasaki, <i>et al.</i>
	AH2	5,117,298	05-26-92	Hirai
	AI2	5,166,816	11-24-92	Kaneko, <i>et al.</i>
	AJ2	5,184,235	02-02-93	Sukegawa
	AK2	5,191,453	03-02-93	Okumura
	AA3	5,206,749	04-27-93	Zavracky, <i>et al.</i>
	AB3	5,233,211	08-03-93	Hayashi, <i>et al.</i>
	AC3	5,317,433	05-31-94	Miyawaki, <i>et al.</i>

EXAMINER	DATE CONSIDERED
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	APPLICANT Duy-Phach Vu, et al.			
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
AR	Akiyama, M., <i>et al.</i> , "Growth of GaAs on Si and Its Application to Fets and LEDs.", <u>Nat. Res. Soc. Symp. Proc.</u> , 67:53-64 (1986).	
AS	Allen, <i>et al.</i> , "Characterization of Isolated Silicon Epitaxy Material", <i>SPIE</i> , Vol. 945 - Advanced Processing of Semiconductor Devices II (3/17-3/18, 1988).	
AT	Conference Record of the 1991 International Display Research Conference, October 15-17, 1991, <i>IEEE</i> .	
AU	Fan, <i>et al.</i> , "Lateral Epitaxy by Seeded Solidification for Growth of Crystal Si Films on Insulators", <u>Appl. Phys. Lett.</u> , 38, 365, 3-1-81.	
AV	McClelland, <i>et al.</i> , "A Technique for Producing Epitaxial Films on Reusable Substrates", <u>Appl. Phys. Lett.</u> , 37, 560, 9-15-80.	
AW	McDaniel, D.L., <i>et al.</i> , "Vertical Cavity Surface-Emitting Semi-Conductor Laser with CW Injection Laser Pumping", <u>IEEE Photon Technol. Lett.</u> , March 23, 1990.	
AX	Milnes, A.G., "Semiconductor Heterojunction Topics: Introduction and Overview", <u>Solid State Electronics</u> , Vol. 29, 2:99-121 (1986).	
AY	Turner, G., <i>et al.</i> , "High-Speed Photoconductive Detectors Fabricated in Heteroepitaxial GaAs Layers", <u>Mat. Res. Soc. Symp. Proc.</u> , 67:181188 (1986).	
AZ	Weber, J.P., <i>et al.</i> , "Effects of Layer Thickness Variations on Vertical Cavity Surface-Emitting DBR Semiconductor Lasers", <u>IEEE Photon Tech. Ltr.</u> , March 23, 1990.	
AR2	Yablonovitch, <i>et al.</i> , "Extreme Selectivity in the Lift-Off of Epitaxial GaAs Films", <u>Appl. Phys. Lett.</u> , 51, 2222 12-28-87.	
AS2	Sumiyoshi, <i>et al.</i> , Device Layer Transferred Poly Si TFT Array for High Resolution Liquid Crystal Projector", <i>IEEE</i> , 7.3.1-7.3.4, 1989.	
AT2	Y. Hayashi, <i>et al.</i> , "A New Three Dimensional IC Fabrication Technology, Stacking This Film Dual-CMOS Layers", <i>IEEE IDRM</i> , pps. 657-660, 1991.	
AU2	"3-D Chip on Chip Stacking", <u>Semiconductor International</u> , December 1991.	

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